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HIGH-SPEED 1.8V 32K x 16 **ASYNCHRONOUS DUAL-PORT** STATIC RAM

IDT70P27L

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed access
 - Commercial: 12/15ns (max.)
 - Industrial: 15ns (max.)
- Low-power operation - IDT70P27L
 - Active: 306mW (typ.)
 - Standby: 360µW (typ.)
- ٠ Separate upper-byte and lower-byte control for bus matching capability
- Dual chip enables allow for depth expansion without external logic
- IDT70P27 easily expands data bus width to 32 bits or more using the Master/Slave select when cascading more than one device

- $M/\overline{S} = VIH$ for \overline{BUSY} output flag on Master, ٠ $M/\overline{S} = VIL$ for \overline{BUSY} input on Slave
- ٠ **Busy and Interrupt Flags**
- ٠ On-chip port arbitration logic
- ٠ Full on-chip hardware support of semaphore signaling between ports
- ٠ Fully asynchronous operation from either port
- ٠ LVTTL-compatible, single 1.8V (1.7V ≤ VDD ≤ 1.95V) power supply
- ٠ Available in 100-pin Thin Quad Flatpack (TQFP)
- ٠ Industrial temperature range (-40°C to +85°C) is available for selected speeds
- ٠ Green parts available, see ordering information



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NOTES:

1) BUSY is an input as a Slave (M/S=VIL) and an output as a Master (M/S=VIH). 2) BUSY and INT are non-tri-state totem-pole outputs (push-pull).

JANUARY 2009

High-Speed 1.8V 32K x 16 Asynchronous Dual-Port Static RAM Description:

systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-

bit or wider memory system applications results in full-speed, error-free

The device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for Commercial and Industrial Temperature Range

The IDT70P27 is a high-speed 32K x 16 Dual-Port Static RAM, designed to be used as a stand-alone 512K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit and wider word combination MASTER/SLAVE Dual-Port RAM for 32-bit and wider word stand by the chip enables (CEo and CE1) permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 306mW of power. The IDT70P27 is packaged in a 100-pin Thin Quad Flatpack (TQFP).

Pin Configurations^(1,2,3)

operation without the need for additional discrete logic.



NOTES:

- 1. All VDD pins must be connected to power supply.
- 2. All Vss pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	CEOR, CE1R	Chip Enable		
R/WL	R/WR Read/Write Enable			
ŌĒL	OER Output Enable			
Aol - A14L	A0R - A14R	Address		
I/O0L - I/O15L	5L VOor - VO15R Data Input/Output			
SEML	SEMR Semaphore Enable			
ŪBL	ŪBR	Upper Byte Select		
LB L	LB R	Lower Byte Select		
ĪNTL	ĪNTR	Interrupt Flag		
BUSYL	BUSYR	Busy Flag		
M/S		Master or Slave Select		
V	DD	Power (1.8V)		
V	SS	Ground (0V)		

5694 tbl 01

Commercial and Industrial Temperature Range

Truth Table I – Chip Enable^(1,2,3)

CE	CE 0	CE1	Mode		
	V⊫	Viн	Port Selected (TTL Active)		
L	<u><</u> 0.2V	<u>></u> Vdd -0.2V	Port Selected (CMOS Active)		
	Vн	Х	Port Deselected (TTL Inactive)		
	Х		Port Deselected (TTL Inactive)		
Н	<u>></u> Vdd -0.2V	Х	Port Deselected (CMOS Inactive)		
	Х	<u><</u> 0.2V	Port Deselected (CMOS Inactive)		

NOTES:

1. Chip Enable references are shown above with the actual \overline{CE}_0 and CE_1 levels, \overline{CE} is a reference only.

2. Port "A" and "B" references are located where $\overline{\text{CE}}$ is used.

3. "H" = VIH and "L" = VIL

Truth Table II - Non-Contention Read/Write Control

		Inpu	uts ⁽¹⁾			Outputs		
CE ⁽²⁾	R/₩	ŌĒ	ŪB	ĹΒ	SEM	I/O8-15	I/O0-7	Mode
Н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
Х	Х	Х	Н	Н	Н	High-Z	High-Z	Both Bytes Deselected
L	L	Х	L	Н	Н	DATAIN	High-Z	Write to Upper Byte Only
L	L	Х	Н	L	Н	High-Z	DATAIN	Write to Lower Byte Only
L	L	Х	L	L	Н	DATAIN	DATAIN	Write to Both Bytes
L	Н	L	L	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	Н	L	Н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	Н	L	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES: 1. AoL — A14L \neq AoR — A14R. 2. Refer to Chip Enable Truth Table.

Truth Table III - Semaphore Read/Write Control

		Inpu	uts ⁽¹⁾			Outputs		
CE ⁽²⁾	R/₩	ŌĒ	ŪB	LB	SEM	I/O8-15	I/O0-7	Mode
Н	Н	L	Х	Х	Ц	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Н	\uparrow	Х	Х	Х	L		DATAIN	Write I/Oo into Semaphore Flag
Х	\uparrow	Х	Н	Н	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L	Х	L			Not Allowed
L	Х	Х	Х	L	L			Not Allowed

NOTES:

1. There are eight semaphore flags written to I/Oo and read from all the I/Os (I/Oo-I/O15). These eight semaphore flags are addressed by Ao-A2.

2. Refer to Chip Enable Truth Table.

5694 tbl 04

5694 tbl 03

5694 tbl 02

High-Speed 1.8V 32K x 16 Asynchronous Dual-Port Static RAM

Commercial and Industrial Temperature Range

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to VDDMAX +0.3V	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Ιουτ	DC Output Current	50	mA

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed VDD + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 0.3V.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0mhz)TQFPONLY$

Symbol	Parameter	Conditions	Max.	Unit		
Cin	Input Capacitance	VIN = 0V	9	рF		
Cout ⁽²⁾ Output Capacitance		Vout = 0V	10	pF		
5694 tbl 08						

NOTES:

1. This parameter is determined by device characterization but is not production tested.

2. Cout also reference Ci/o.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	1.7V <u><</u> Vdd <u><</u> 1.95V
Industrial	-40°C to +85°C	0V	1.7V <u><</u> Vdd <u><</u> 1.95V
			5694 tbl 06

NOTES:

5694 tbl 05

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions⁽¹⁾

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Supply Voltage	1.7	1.8	1.95	V
Vss	Ground	0	0	0	V
V⊪	Input High Voltage	0.7Vdd	1	VDD+0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾		0.3Vdd	۷

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns. 2. VTERM must not exceed VDD + 0.3V.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (1.7V \leq VDD \leq 1.95V)

			70P	27L	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	V_{DD} = 1.95V, V_{IN} = 0V to V_{DD}	_	5	μA
Ilo	Output Leakage Current	\overline{CE} = VIH, VOUT = 0V to VDD	_	5	μA
Vol	Output Low Voltage	Iol = 2mA	_	0.45	V
Vон	Output High Voltage	юн = -2mA	Vdd - 0.45	_	V

5694 tbl 09

5694 tbl 07

Commercial and Industrial Temperature Range

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾ $(1.7V \le VDD \le 1.95V)$

					27L12 I Only	70P27L15 Com'l & Ind			
Symbol	Parameter	Test Condition	Versi	on	Тур.	Мах.	Тур.	Max.	Unit
IDD	Dynamic Operating Current	CE = V⊾, Outputs Disabled SEM = V⊮	COM'L	L	175	230	170	225	mA
	(Both Ports Active)	$f = fMAX^{(3)}$	IND'L	L			170	235	
ISB1	Standby Current (Both Ports - TTL Level		COM'L	L	12	20	10	18	mA
	Inputs)		IND'L	L			44	65	
ISB2	Standby Current (One Port - TTL Level	$\overline{CE}^{*}A^{*} = V_{IL}$ and $\overline{CE}^{*}B^{*} = V_{IH}^{(5)}$ Active Port Outputs Disabled,	COM'L	L	125	150	115	145	mA
Inputs) f=fr	$\frac{f=f_{MAX}^{(3)}}{\overline{SEM}_{R}} = \overline{SEM}_{L} = V_{IH}$	IND'L	L	_		115	155		
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports $\overline{CE}L$ and $\overline{CE}R \ge V_{DD} - 0.2V$ $V_{IN} \ge V_{DD} - 0.2V$ or	COM'L	L	0.2	5	0.2	5	mA
CMOS Leve		$\frac{V_{IN} \leq 0.2V, f = 0^{(4)}}{SEM_R} = \overline{SEM}_L \geq V_{DD} - 0.2V$	IND'L	L			0.2	6	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\label{eq:constraint} \begin{array}{ c c c c c c c c c c c c c c c c c c c$	COM'L	L	125	150	115	140	m/
	SET R = SET \geq VDD - 0.2V VIN \geq VDD - 0.2V or VIN \leq 0.2V Active Port Outputs Disabled f = fMAX ⁽³⁾	IND'L	L			115	145		

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V.

2. f = 0 means no address or control lines change.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Refer to Chip Enable Truth Table.

AC Test Conditions

	5694 tbl 11
Output Load	Figures 1 and 2
Output Reference Levels	0.9V
Input Timing Reference Levels	0.9V
Input Rise/Fall Times	3ns Max.
Input Pulse Levels	GND to 1.8V



Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLz, tHz, twz, tow) *Including scope and jig

Commercial and Industrial Temperature Range

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

			27L12 I Only	70P27L15 Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
READ CYC	CLE						
trc	Read Cycle Time	12		15		ns	
taa	Address Access Time		12		15	ns	
t ACE	Chip Enable Access Time ⁽³⁾		12		15	ns	
tabe	Byte Enable Access Time ⁽³⁾		12		15	ns	
taoe	Output Enable Access Time		9		10	ns	
tон	Output Hold from Address Change	3		3		ns	
t∟z	Output Low-Z Time ^(1,2)	3	_	3		ns	
tнz	Output High-Z Time ^(1,2)		10		12	ns	
tPU	Chip Enable to Power Up Time ^(2,4)	0		0		ns	
tPD	Chip Disable to Power Down Time ^(2,4)		12		15	ns	
tSOP	Semaphore Flag Update Pulse (OE or SEM)	8		10		ns	
tsaa	Semaphore Address Access Time		12		15	ns	

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested. 3. To access RAM, $\overline{CE} = VIL$ and $\overline{SEM} = VIH$. To access semaphore, $\overline{CE} = VIH$ and $\overline{SEM} = VIL$.

4. Refer to Chip Enable Truth Table.

5694 tbl 12a

Commercial and Industrial Temperature Range

tRC ADDR tAA⁽⁴⁾ tACE⁽⁴⁾ $\overline{\mathsf{CE}}^{(6)}$ taoe⁽⁴⁾ ŌĒ tabe⁽⁴⁾ UB, LB R/W ton tLZ⁽¹⁾ VALID DATA DATAOUT tHZ⁽²⁾ BUSYOUT ⁻ tBDD^(3,4) 5694 drw 05

Waveform of Read Cycles⁽⁵⁾

Timing of Power-Up Power-Down



NOTES:

- 1. Timing depends on which signal is asserted last: \overline{CE} , \overline{OE} , \overline{LB} , or \overline{UB} . 2. Timing depends on which signal is de-asserted first: \overline{CE} , \overline{OE} , \overline{LB} , or \overline{UB} .
- 3. teod delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. SEM = VIH.
- 6. Refer to Chip Enable Truth Table.

NOTES:

High-Speed 1.8V 32K x 16 Asynchronous Dual-Port Static RAM

Commercial and Industrial Temperature Range

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage

			70P27L12 Com'l Only		70P27L15 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CY	CLE					
twc	Write Cycle Time	12		15		ns
tew	Chip Enable to End-of-Write ⁽³⁾	9		12		ns
taw	Address Valid to End-of-Write	9		12	_	ns
tas	Address Set-up Time ⁽³⁾	0		0		ns
twp	Write Pulse Width	9		12		ns
twr	Write Recovery Time	0		0	_	ns
tow	Data Valid to End-of-Write	8		10		ns
tHZ	Output High-Z Time (1,2)		8		10	ns
tDH	Data Hold Time ⁽⁴⁾	0		0	_	ns
twz	Write Enable to Output in High-Z ^(1,2)		8	_	10	ns
tow	Output Active from End-of-Write (1,2,4)	0		0		ns
tswrd	SEM Flag Write to Read Time	5		5		ns
tsps	SEM Flag Contention Window	5		5		ns

5694 tbl 13a

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

3. To access RAM \overrightarrow{CE} = VIL and \overrightarrow{SEM} = VIH. To access semaphore, \overrightarrow{CE} = VIH and \overrightarrow{SEM} = VIL. Either condition must be valid for the entire tew time. Refer to Chip Enable Truth Table.

4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

Commercial and Industrial Temperature Range

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,5,8)



5694 drw 07

Timing Waveform of Write Cycle No. 2, **CE**, **UB**, **LB** Controlled Timing^(1,5)



NOTES:

1. $R\overline{W}$ or \overline{CE} or \overline{UB} and \overline{LB} must be HIGH during all address transitions.

2. A write occurs during the overlap (tew or twp) of a LOW CE and a LOW R/W for memory array writing cycle.

- 3. twr is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .

7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).

8. If \overline{OE} is LOW during R \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If \overline{OE} is HIGH during an R \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. TEW must be met for either condition.

10. Refer to Chip Enable Truth Table.

High-Speed 1.8V 32K x 16 Asynchronous Dual-Port Static RAM Commercial and Industrial Temperature Range

Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾



NOTES:

1. $\overline{CE} = V_{IH}$ or \overline{UB} and $\overline{LB} = V_{IH}$ for the duration of the above timing (both write and read cycle), refer to Chip Enable Truth Table.

2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



NOTES:

1. DOR = DOL = VIL, $\overline{CER} = \overline{CEL} = VIH$, or both $\overline{UB} \& \overline{LB} = VIH$ (refer to Chip Enable Truth Table).

2. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

3. This parameter is measured from R/W"A" or SEM"A" going HIGH to R/W"B" or SEM"B" going HIGH.

4. If tsps is not satisfied, there is no guarantee which side will be granted the semaphore flag.

Commercial and Industrial Temperature Range

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

	Parameter Min. Max.				70P27L15 Com'l & Ind	
Symbol			Мах.	Min.	Мах.	Unit
BUSY TIM	ING (M/S=Vih)					
t BAA	BUSY Access Time from Address Match		12		15	ns
t BDA	BUSY Disable Time from Address Not Matched		12		15	ns
t BAC	BUSY Access Time from Chip Enable Low		12		15	ns
tbdc	BUSY Disable Time from Chip Enable High		12		15	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5		ns
t BDD	BUSY Disable to Valid Data ⁽³⁾		12		17	ns
twн	Write Hold After BUSY ⁽⁵⁾	12		12		ns
BUSY TIM	ING (M/S=VIL)					
twв	BUSY Input to Write ⁽⁴⁾	0		0		ns
twн	Write Hold After BUSY ⁽⁵⁾	12		12		ns
PORT-TO-I	PORT DELAY TIMING					
twdd	Write Pulse to Data Delay ⁽¹⁾		20		30	ns
todd	Write Data Valid to Read Data Delay ⁽¹⁾		20		25	ns
	•		•	•		5694 tbl 14

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VI-)".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual), or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

Commercial and Industrial Temperature Range

Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}^{(2,5)}$ (M/ $\overline{\text{S}} = \overline{\text{VIH}}$)⁽⁴⁾



NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = V_{IL}$ (SLAVE).
- 2. $\overline{CE}L = \overline{CE}R = VIL$ (refer to Chip Enable Truth Table).
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If M/S = VIL (SLAVE), then BUSY is an input. Then for this example BUSY "A"= VIH and BUSY "B"= input is shown above.

5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform Write with **BUSY** (M/ \overline{S} = VIL)



NOTES:

- 1. twn must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the "Slave" version.



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing $(M/S = VIH)^{(1)}$



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. If tAPS is not satisfied, the busy signal will be asserted on one side or another but there is no guarantee on which side busy will be asserted.

3. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

		70P27L12 Com'l Only		70P27L15 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Мах.	Unit
INTERRUPT						
tas	Address Set-up Time	0	_	0	_	ns
twr	Write Recovery Time		_	0		ns
tins	Interrupt Set Time		12		15	ns
tinr	Interrupt Reset Time	-	20		25	ns

5694 tbl 15a

High-Speed 1.8V 32K x 16 Asynchronous Dual-Port Static RAM Waveform of Interrupt Timing^(1,5)



Commercial and Industrial Temperature Range

NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. See Interrupt Truth Table.
- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last. 4. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is de-asserted first.
- 5. Refer to Chip Enable Truth Table.

Left Port				- Right Port						
R/₩L	CEL	ŌĒL	A14L-A0L	ĪNTL	R/WR	CER	ŌĒr	A14R-A0R	ĪNTR	Function
L	L	Х	7FFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
х	Х	Х	Х	Х	Х	L	L	7FFF	H ⁽³⁾	Reset Right INTR Flag
х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FFE	Х	Set Left INT∟ Flag
х	L	L	7FFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

Truth Table IV — Interrupt Flag^(1,4)

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = V_{IH}$.

2. If $\overline{BUSY}_{L} = V_{IL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = \text{VIL}$, then no change.

4. Refer to Chip Enable Truth Table.

High-Speed 1.8V 32K x 16 Asynchronous Dual-Port Static RAM

Truth Table V — Address **BUSY** Arbritration⁽⁴⁾

Inputs			Out	puts	
CEL	CE R	Aol-A14L Aor-A14r	BUSYL ⁽¹⁾	BUSY _R ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70P27 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

2. "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

4. Refer to Chip Enable Truth Table.

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2)

5694 tbl 17

Functions	D0 - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70P27.

2. There are eight semaphore flags written to via I/O0 and read from all the I/O's (I/O0-I/O15). These eight semaphores are addressed by Ao - A2.

Functional Description

The IDT70P27 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70P27 has an automatic power down feature controlled by \overline{CE}_0 and CE_1 . The \overline{CE}_0 and CE_1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INT}_L) is asserted when the right port writes to memory location 7FFE (HEX), where a write is defined as $\overline{CE}_R = R/\overline{W}_R = VIL$ per the Truth Table IV. The left port clears the interrupt through access of address location

7FFE when $\overline{CE}_{L} = \overline{OE}_{L} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INT}_{R}) is asserted when the left port writes to memory location 7FFF (HEX) and to clear the interrupt flag (\overline{INT}_{R}), the right port must read the memory location 7FFF. The message (16 bits) at 7FFE or 7FFF is user-defined since it is an addressable SRAM location. If the interrupt func-tion is not used, address locations 7FFE and 7FFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table IV for the interrupt operation.

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Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on

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the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW.

The BUSY outputs on the IDT 70P27 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

Width Expansion with **BUSY** Logic Master/Slave Arrays



Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70P27 RAMs.

When expanding an IDT70P27 RAM array in width while using \overline{BUSY} logic, one master part is used to decide which side of the RAM array will receive a \overline{BUSY} indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the busy signal as a write inhibit signal. Thus on the IDT70P27 RAM the \overline{BUSY} pin is an output if the part is used as a master (M/S pin = VIH), and the \overline{BUSY} pin is an input if the part is used as a slave (M/S pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating $\overline{\text{BUSY}}$ on one side of the array and another master indicating $\overline{\text{BUSY}}$ on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with either the R/W signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70P27 is a fast Dual-Port 32K x 16 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by CE the Dual-Port RAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table II where CE and SEM are both HIGH.

Systems which can best use the IDT70P27 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70P27's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70P27 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

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The semaphore flags are active low. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70P27 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{OE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0–A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table VI). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able towrite a zero into a semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as a one, a fact which the processor will verify by the subsequent read (see Table VI). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during the subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The



reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag low and the other side high. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay low until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

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Ordering Information



NOTES:

1. Industrial temperature range is available on selected TQFP packages in low power. For other speeds, packages and powers contact your sales office.

2. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History

04/02/08:	Initial Release	
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